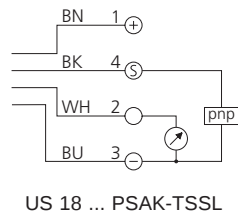
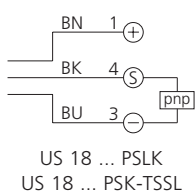


Ultraschall-Sensoren | Ultrasonic sensors

- Stabiles Gehäuse
 - Arbeitsbereich einstellbar
 - Schmutzunempfindlich
 - Störgeräuschunempfindlich
 - Messung oberflächenunabhängig
 - Schalt- und Analogausgang
 - Hohe Folgegeschwindigkeit
 - Hohe Auflösung
 - Piezokeramischer Verbundwandler
-
- Robust casing
 - Scanning range adjustable
 - Insensitive to dirt
 - Insensitive to ambient noise
 - Scanning does not depend on surface
 - Binary and analog output
 - High follow-up speed
 - High resolution
 - Piezo-ceramic composite transducer

Anschlusschema Connection diagram

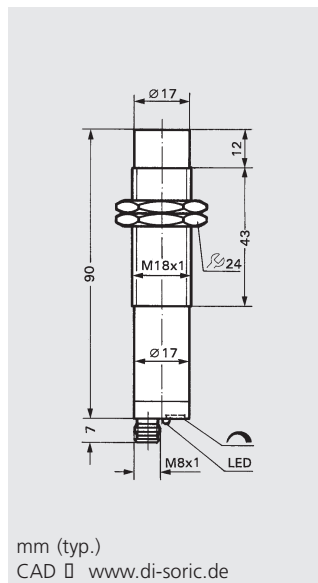
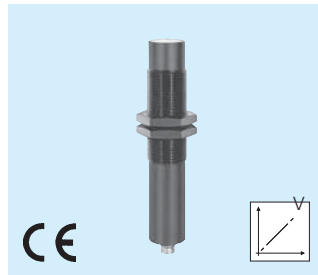


BN = Braun / brown
BK = Schwarz / black

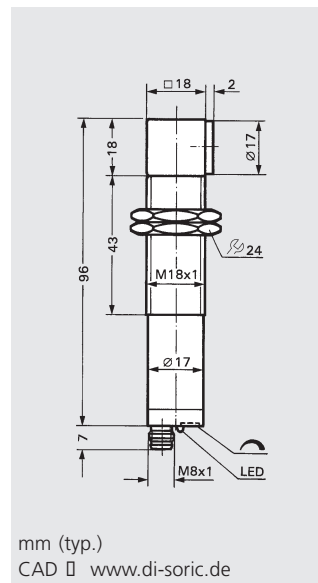
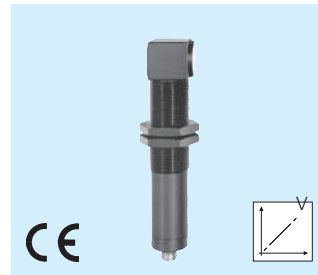
Technische Daten	Technical Data	bei + 20 °C, 24 V DC / at + 20 °C, 24 V DC
Arbeitsbereich	Scanning range	
Sendefrequenz	Operating frequency	
Betriebsspannung	Service voltage	
Eigenstromaufnahme	Internal power consumption	
Schaltausgang	Binary output	
Schaltfrequenz	Switching frequency	
Ansprech- / Abfallzeit	Response / release time	
Schalthysterese axial	Switching hysteresis axial	
Genauigkeit	Accuracy	
Analogausgang	Analog output	
Linearität Analogausgang	Linearity analog output	
Temperaturdrift Analogausgang	Temperature drift analog output	
Temperaturdrift Luftstrecke	Temperature drift air path	
Lastwiderstand	Load resistance	
Welligkeit	Ripple	
Folgegeschwindigkeit	Follow-up speed	
Umgebungstemperatur	Ambient temperature	
Schutzart	Protection class	
Gehäusematerial	Casing material	

Bestelltabelle	Ordering Table	Typ / Model
Ausgang	Output	
NO	NO	
NO + analog	NO + analog	
Anschlusskabel (sep. Datenblatt)	Connecting cable (sep. data-sheet)	

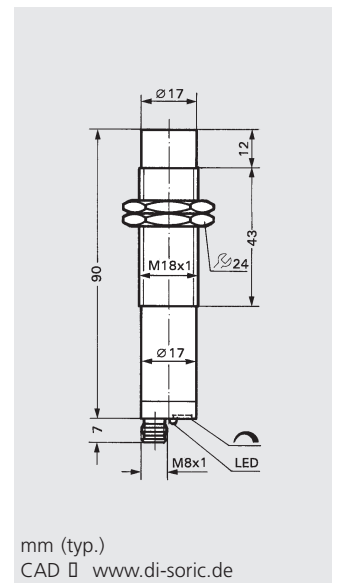
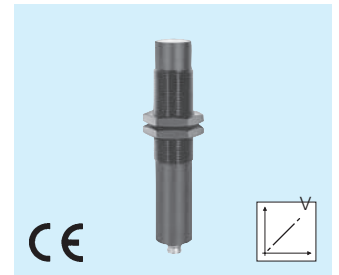
Arbeitsbereich 1000 mm
Scanning range



Arbeitsbereich 1000 mm
Scanning range



Arbeitsbereich 1000 mm
Scanning range



160 ... 1000 mm

180 kHz

18 ... 33 V DC

ca. 45 mA

Transistor pnp, 100 mA, NO

ca. 16 Hz

< 70 ms

30 ... 40 mm

± 2 % / Sn max.

1,6 ... 10 V

< 1 % / Sn max.

typ. + 4 mV/K

- 0,17 %/K

> 10 kΩ

ca. ± 120 mV

< 100 ms (95% Sn max.)

-20 ... +50 °C

IP 67

Polyamid / polyamide

160 ... 1000 mm

180 kHz

18 ... 33 V DC

ca. 45 mA

Transistor pnp, 100 mA, NO

ca. 16 Hz

< 70 ms

30 ... 40 mm

± 2 % / Sn max.

1,6 ... 10 V

< 1 % / Sn max.

typ. + 4 mV/K

- 0,17 %/K

> 10 kΩ

ca. ± 120 mV

< 100 ms (95% Sn max.)

-20 ... +50 °C

IP 67

Polyamid / polyamide

180 ... 1000 mm

180 kHz

18 ... 33 V DC

ca. 35 mA

Transistor pnp, 100 mA, NO

ca. 7 Hz

< 100 ms

30 ... 60 mm

± 2 % / Sn max.

1,8 ... 10 V

< 1 % / Sn max.

typ. + 4 mV/K

- 0,17 %/K

> 10 kΩ

ca. ± 100 mV

< 400 ms (95% Sn max.)

-20 ... +50 °C

IP 67

Polyamid / polyamide

US 18 K 1000 PSAK-TSSL

TK ... /4

US 18 KR 1000 PSAK-TSSL

TK ... /4

US 18 K 1003 PSAK-TSSL

TK ... /4